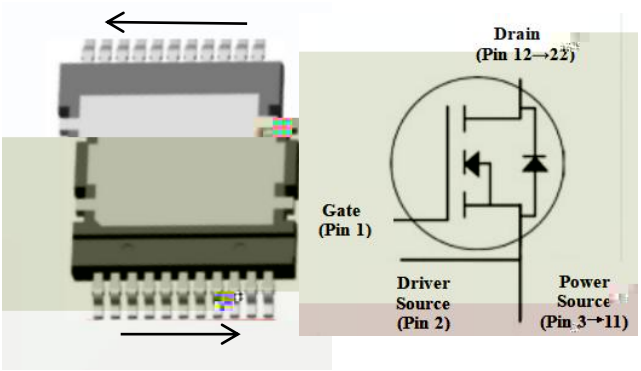
SG2M018120WJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-
-
-



Benefits

-
-
-
-
-

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	Package

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1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

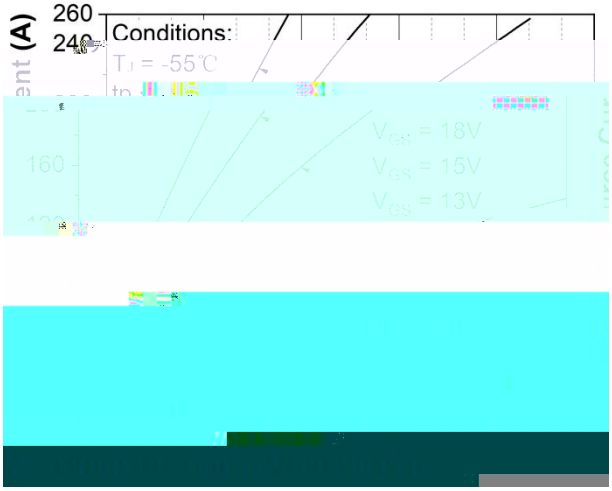
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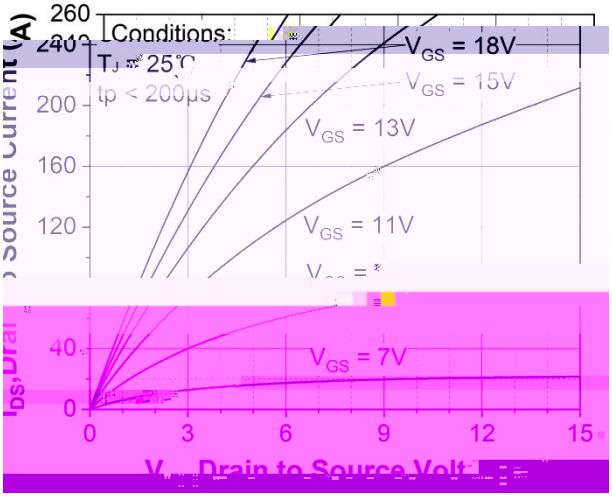
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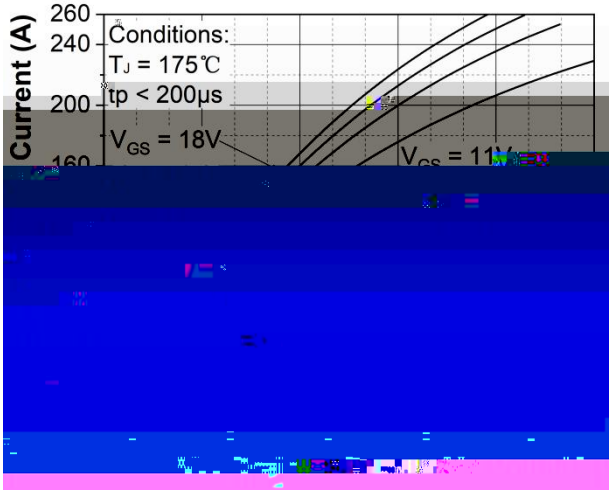
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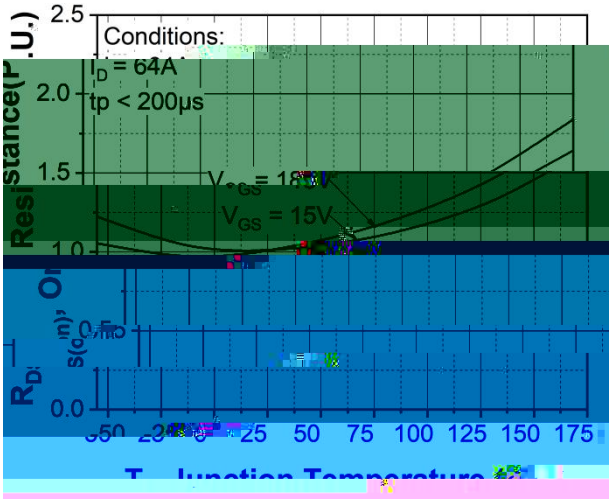
1200V SiC Power MOSFEa

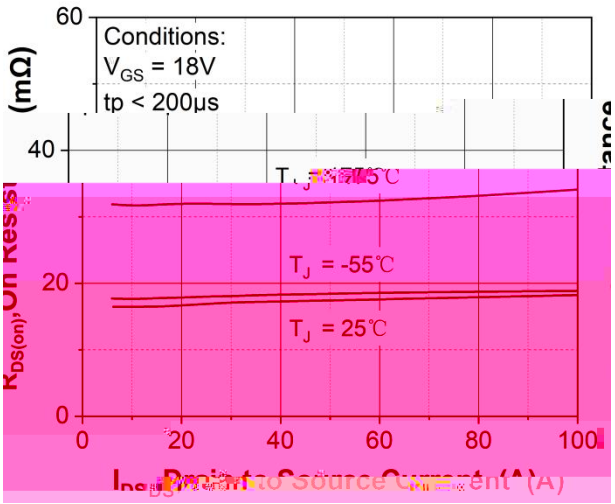
4 Electrical characteristic diagrams

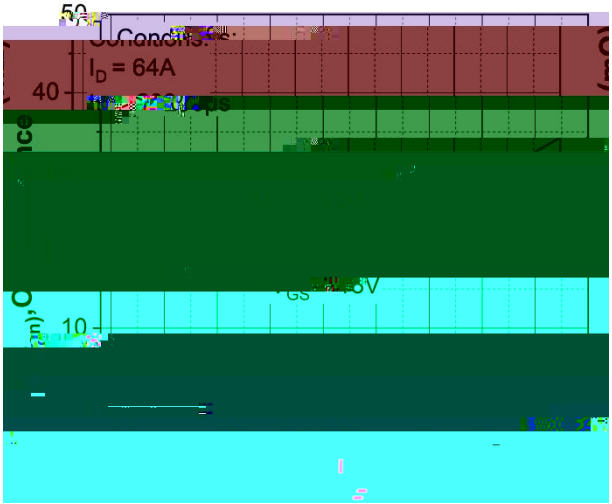




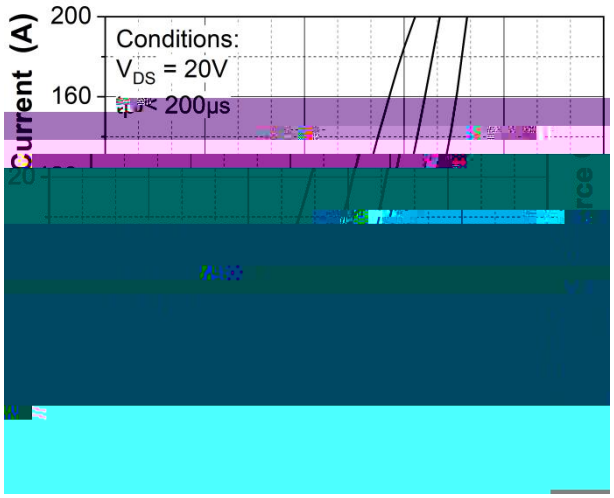


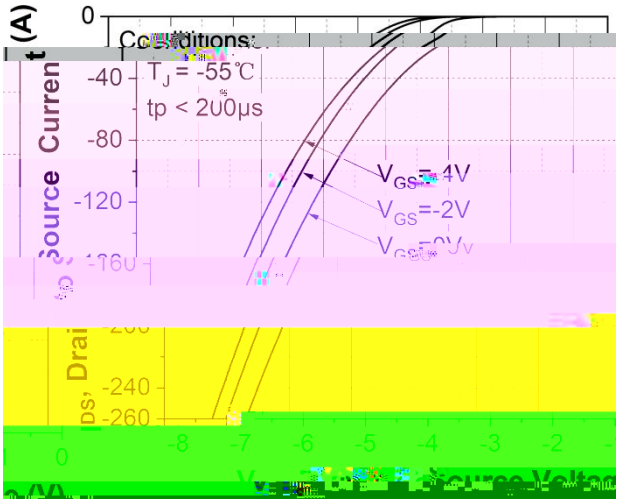


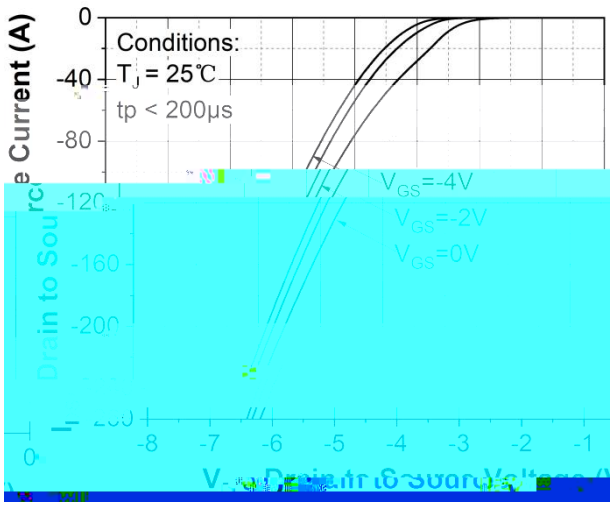


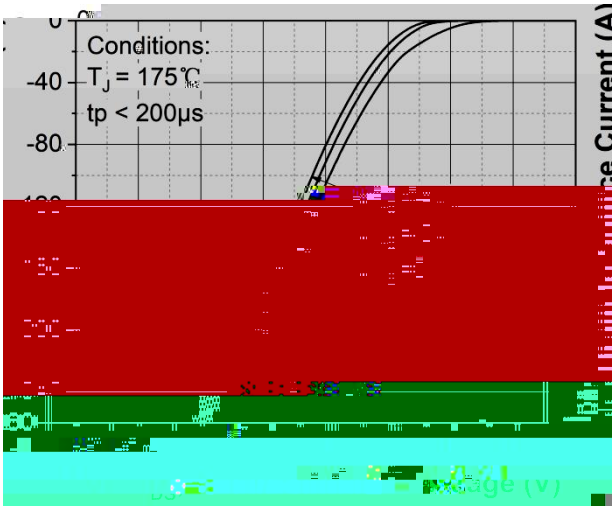


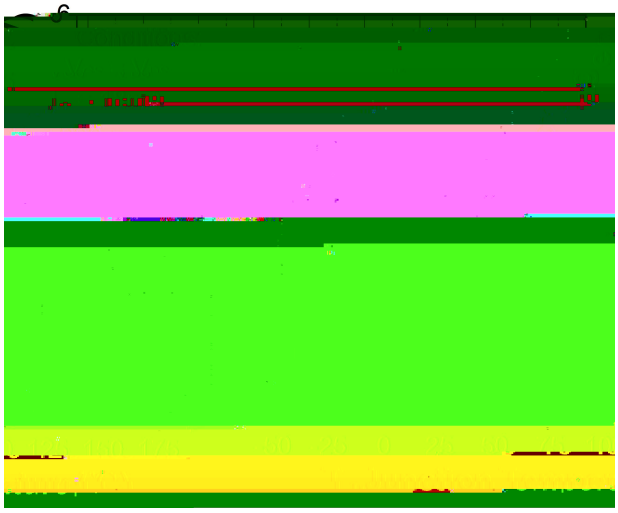
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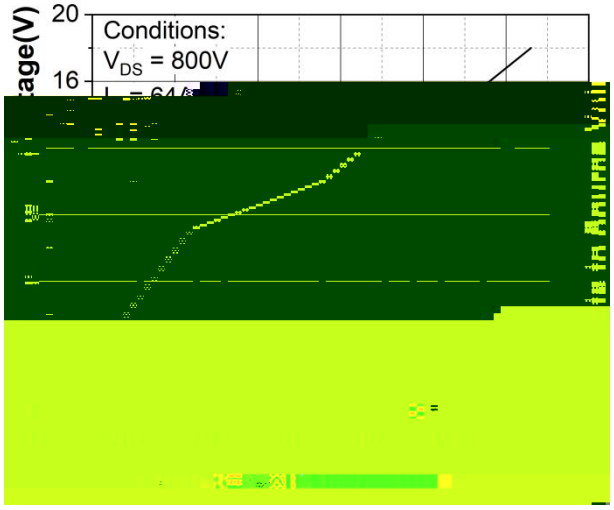




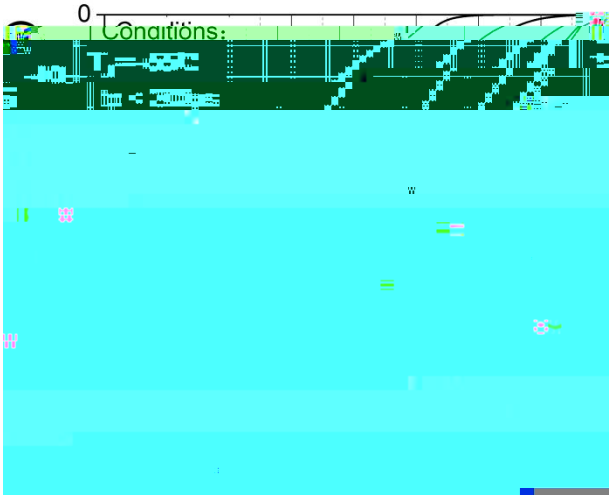


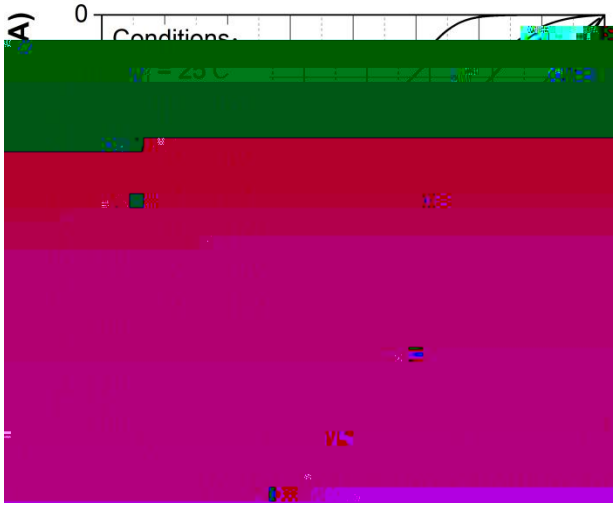


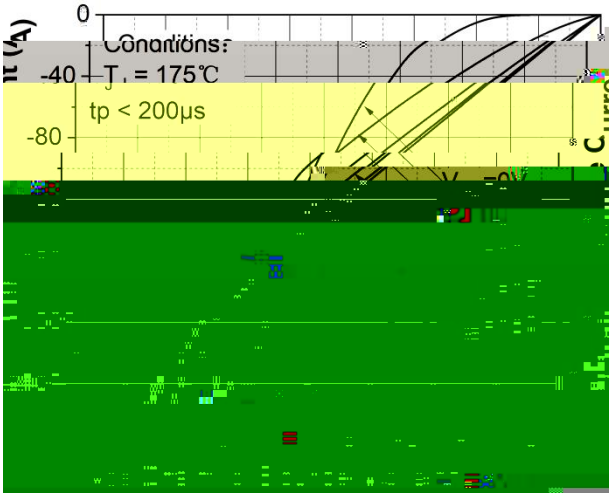


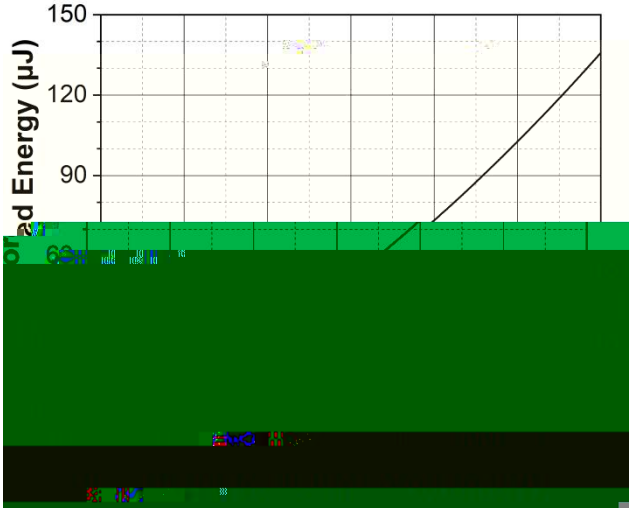


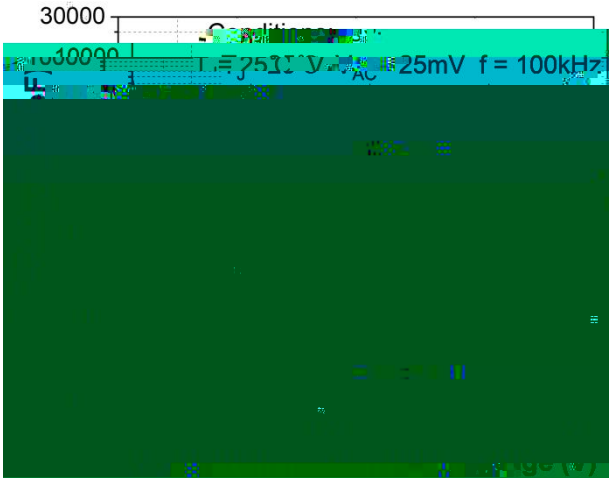
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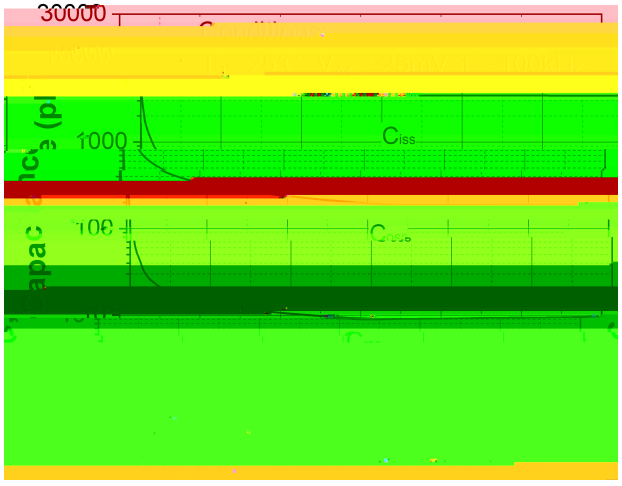






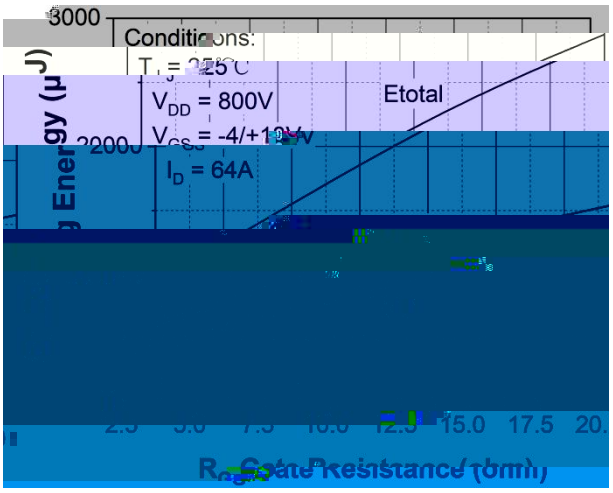


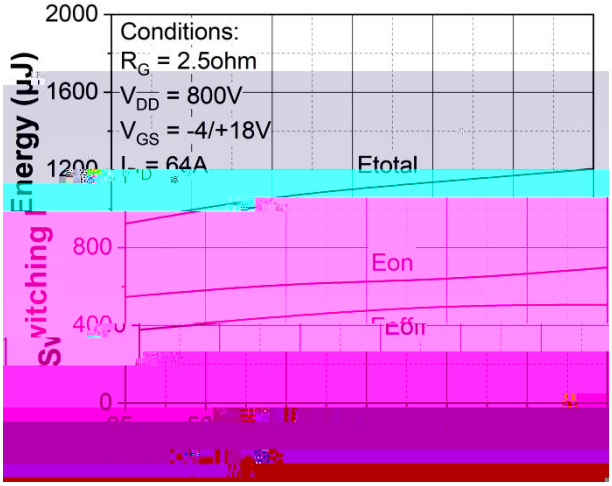


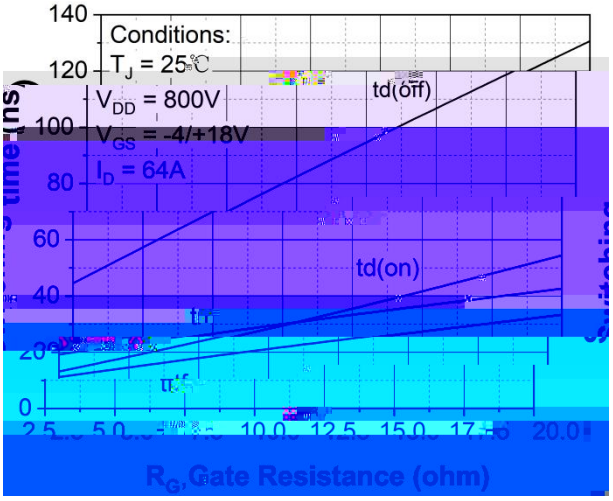


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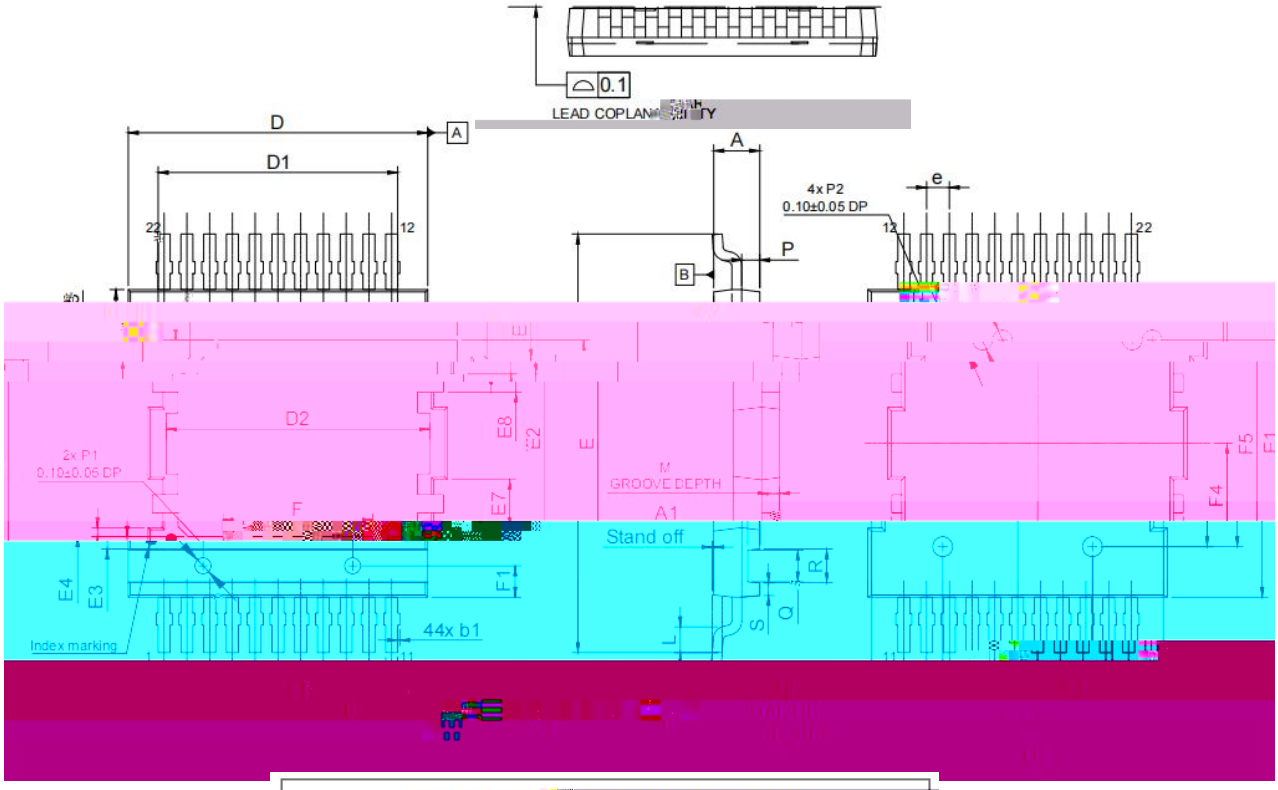
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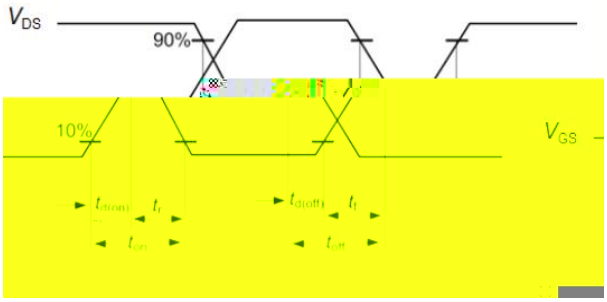


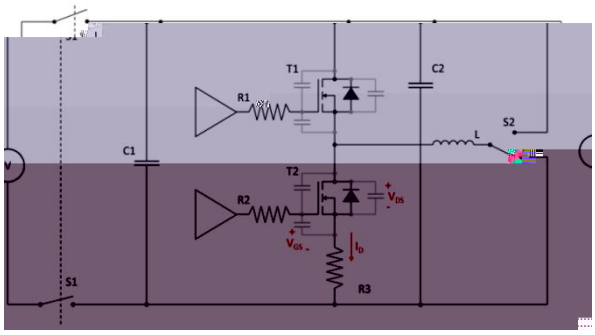
5 Package drawing



CONTROLLING DIMENSION :MILLIMETERS					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.25	2.35	E9		0.75
A1	0.00	0.15	e	1.14	
A2	0.90		e1	11.4	
A3	0.50		F	7.40	7.60
b	0.50	0.70	F1	1.47	1.67
b1	-	0.15	F2	7.40	7.60
c	0.48	0.58	F3	3.65	3.85
D	14.90	15.10	F4	5.07	5.27
D1	12.00		F5	10.24	10.44
D2	13.20		L	1.30	
D3	14.50	14.70	M	0.60	
E	20.81	21.11	N	22	
E1	15.30	15.50	O	0	8°
E2	0.80		P	0.00	0.10
E3	0.40	1.20	Q	0.00	1.10
E4	0.90	1.20	R	1.60	
E7	2.53		R	1.70	
E8	2.40		S	0.681	
E9	0.90°				

6 Test conditions





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1200V SiC Power MOSFE.

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